

R-C Thermal Model Parameters

DESCRIPTION

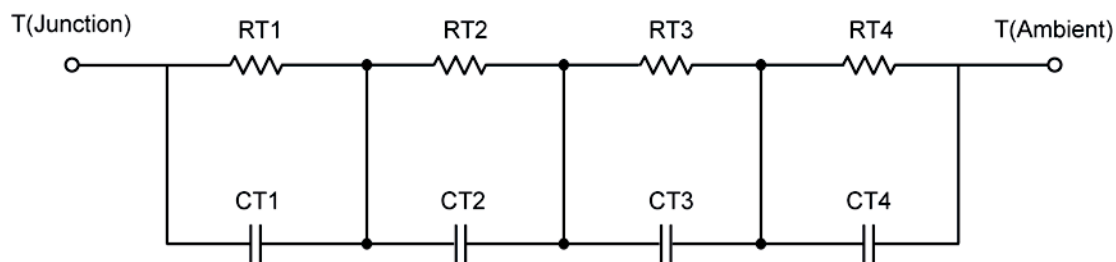
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

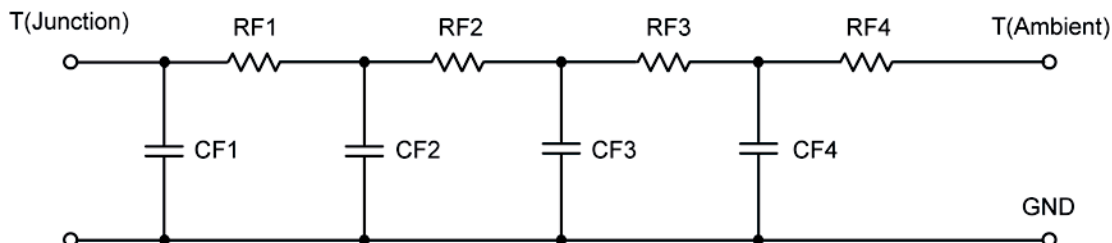
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	10.8700	N/A	8.0367
RT2	5.7169	N/A	2.9860
RT3	20.0537	N/A	2.4581
RT4	48.1958	N/A	10.5020
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	27.3588 m	N/A	6.8201 m
CT2	900.4492 u	N/A	433.1994 u
CT3	78.4403 m	N/A	826.5398 m
CT4	1.3102	N/A	96.4489 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	6.9201	N/A	3.1653
RF2	17.8306	N/A	8.5330
RF3	14.4157	N/A	7.2287
RF4	45.6863	N/A	5.2115
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	1.0579 m	N/A	438.9922 u
CF2	21.5519 m	N/A	5.2558 m
CF3	69.1715 m	N/A	60.9340 m
CF4	1.2890	N/A	159.5875 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

